WHAT IS CLAIMED IS:

1. A method for making a monolithic ceramic capacitor, comprising:

(a) providing a pair of first ceramic green sheets and at least one second ceramic green sheet, each of the first ceramic green sheets having a first main surface provided with a thin-film conductive film, each of the first and second ceramic green sheets comprising a ceramic material and a binder, wherein the binder or the amount thereof in the second ceramic green sheet is such that the removal upon heating of the second ceramic green sheet binder commences before that of the first ceramic green sheet binder;

(b) forming a green composite stack in which the second ceramic green sheet is disposed between the two first ceramic green sheets so as not to come into contact with the first main surfaces of the first ceramic green sheets; and

(c) heating the green composite to remove the first binder and the second binder.

2. The method according to claim 1, wherein the content of binder relative to the ceramic is larger in the first ceramic green sheets than in the second ceramic greet sheet.

3. The method according to claim 2, wherein the heated green composite is sintered.

4. The method according to claim 3, wherein the distance between the conductive films of said pair of first green ceramic sheets in the green composite stack is about 0.3 to 1.2 μm.

5. The method according to claim 5, wherein the conductive films comprise nickel and have a thickness of about 0.1 to 0.8 μm, the first and second ceramics comprise the same dielectric barium titanate, and wherein the first and second ceramic green sheets have a thickness of at least about 0.1 μm.

6. The method according to claim 1, wherein the distance between the conductive films of said pair of first green ceramic sheets in the green composite stack is about 0.3 to 1.2 μm.

7. The method according to claim 1, further comprising forming a first ceramic green sheet by applying a slurry comprising the first ceramic green sheet ceramic material and binder to a thin film conductive film disposed on a carrier sheet to form a first ceramic green sheet layer having a first main surface with the conductive film disposed thereon and an opposing second main surface.

8. The method according to claim 7, wherein a second ceramic green sheet slurry comprising the second ceramic green sheet ceramic material and binder is applied to the opposing second main surface of the a first ceramic green sheet slurry layer to form a layer having one surface adjacent the second main surface of the first green sheet layer and an opposing second surface.

9. The method according to claim 8, wherein a slurry comprising the first ceramic green sheet ceramic material and binder is applied to the second surface of the second ceramic green sheet layer so as to form the other member of the pair of first ceramic green sheets.

10. The method according to claim 9, wherein a thin-film conductive film is provided on the first main surface of the other member of the pair of first ceramic green sheets.

11. A method for making a monolithic ceramic capacitor, comprising :

(a) preparing first ceramic green sheets each having a first main surface , the first ceramic green sheets comprising a first ceramic material powder and a first binder;

(b) forming a green composite comprising the following sequentially stacked layers: a thin-film conductive film, at least one first ceramic green sheet having its first main surface facing said film, at least one second ceramic green sheet,

at least one first ceramic green sheet having its first main surface facing away form the second ceramic green sheet, and a thin-film conductive film, wherein the second ceramic green sheet comprise a second ceramic material powder and a second binder, and wherein the second ceramic green sheets is arranged so as not to come into contact with the first main surfaces of the first ceramic green sheets; and

(c) heating the green composite to remove the first binder and the second binder,

wherein the second binder is removed before the first binder is removed.

12. The method according to claim 11, wherein the content of the second binder relative to the second ceramic material powder is smaller than the content of the first binder relative to the first ceramic material powder.

13. The method according to claim 11, wherein the first ceramic green sheets with the conductive films are each prepared by transferring a conductive film disposed on a carrier film onto the first main surface of the first ceramic green sheet.

14. The method according to claim 11, wherein the first ceramic green sheets with the conductive films are each prepared by applying a ceramic slurry comprising the first ceramic material powder and the first binder on the conductive film disposed on a carrier film.

15. The method according to claim 11, wherein a first ceramic slurry comprising the first ceramic material powder and the first binder is applied on the conductive film disposed on a carrier film so as to form a first ceramic green sheet, and a second ceramic slurry comprising the second ceramic material powder and the second binder is applied on the first ceramic green sheet so as to form a second ceramic green sheet.

16. The method according to claim 11, wherein a first ceramic slurry comprising the first ceramic material powder and the first binder is applied on the

conductive film disposed on a carrier film so as to form one of the first ceramic green sheets; a second ceramic slurry comprising the second ceramic material powder and the second binder is applied on the first ceramic green sheet so as to form a second ceramic green sheet; and a first ceramic slurry is applied on the second ceramic green sheet so as to form a ceramic green sheet.

17. The method according to claim 11, wherein the thickness of a dielectric layer disposed between the conductive films is about 0.3 to 1.2 μm.

18. The method according to claim 11, wherein the conductive film is formed by a thin-film forming method selected from the group consisting of vacuum vapor deposition, sputtering, electroplating and electroless plating.

19. The method according to claim 11, wherein the thickness of the conductive films is about 0.1 to 0.8 μm.

20. The method according to claim 11, wherein the conductive films comprise nickel and the first and second ceramics comprise the same dielectric barium titanate.